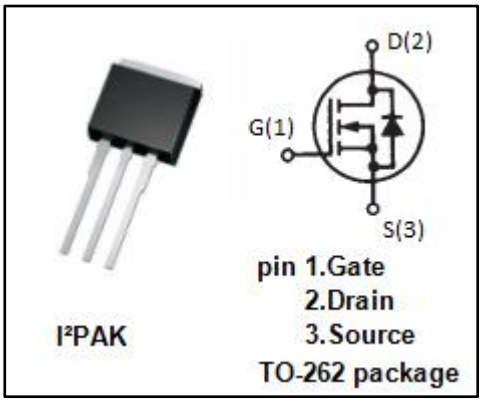
isc N-Channel MOSFET Transistor 2SK3272L



FEATURES

- Drain Current : I_D= 80A@ T_C=25℃
- Drain Source Voltage
  : V_{DSS}= 60V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 6.5mΩ (Max) @VGS= 40V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

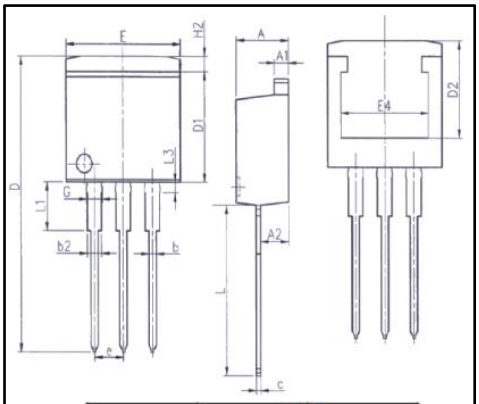
- motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage-Continuous	±30	V
I_D	Drain Current-Continuous	80	A
I_{DM}	Drain Current-Single Pluse	320	A
P_D	Total Dissipation @T_C=25℃	135	W
T_J	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	0.93	℃/W



DIM	MM MIN	MM MAX
A	4.37	4.77
A1	1.22	1.42
A2	2.47	2.87
b	0.7	0.97
b2	1.17	1.42
c	0.28	0.53
D	23.2	24.02
D1	8.38	8.9
D2	6	/
E	9.9	10.39
E4	7.3	/
E	2.54BSC	
G	1.25	1.5
H2	/	1.31
L	13.34	14.1
L1	3.3	4.06
L3	0.95	1.15

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 1mA	60	--	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D= 1mA	2.5	2.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 40V; I_D= 40A	--	6.5	mΩ
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0	--	±0.1	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 60V; V_{GS}= 0	--	0.1	mA
V_{SD}	Forward On-Voltage	I_S=80A; V_{GS}= 0	--	1.5	V